

Supplementary Information: Parity-independent Kondo effect of correlated electrons in electrostatically defined ZnO quantum dots

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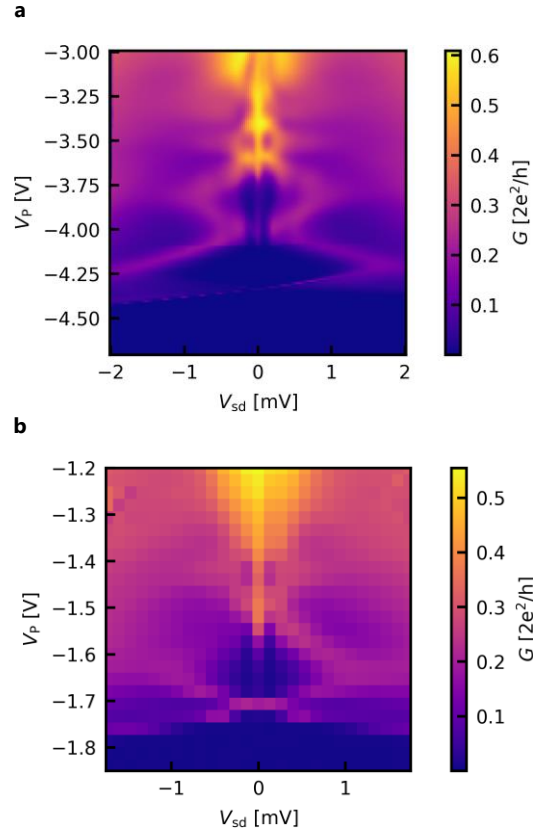
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Supplementary Figure 1. **a, b** Conductance map as functions of V_{sd} and V_p in different devices.

KONDO EFFECTS OBSERVED IN DIFFERENT DEVICES

Supplementary Figure 1a and b show the conductance (G) maps as functions of the source-drain bias V_{sd} and the gate voltage V_p in quantum dot devices different from that used in the main text. We can see the zero-bias Kondo peaks in these devices, which illustrate the robustness of the Kondo effects in ZnO quantum dots. The breakdown of the even-odd electron parity effects is also observed in different devices.

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